













ESD

TVS

TSS

MOV

GDT

PLED

2N7002ET1G-MS

Product specification





Features

- 60V,0.3A, RDS(ON) =2.2Ω@VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

Reference News

Application

- Motor Drive
- Power Tools
- LED Lighting

BVDSS	RDSON	ID
60V	2.2Ω	0.3A

PACKAGE OUTLINE	Pin Configuration	Marking
G SOT-23	G	72K

Absolute Maximum Ratings (TA=25 °C unless otherwise noted)

Symbol	Parameter	Rating	Units
Vds	Drain- Source Voltage	60	V
Vgs	Gate- Source Voltage	±20	V
ID	Drain Current – Continuous (Tc=25℃)	0.3	А
טי	Drain Current – Continuous (Tc=100℃)	0.1	А
Ідм	Drain Current – Pulsed ¹	0.8	А
PD	Power Dissipation (T _C =25°c)	0.35	W
ΓD	Power Dissipation – Derate above 25 ℃	0.003	W/°C
Тѕтс	Storage Temperature Range	-50 to 150	°C
TJ	Operating Junction Temperature Range	-50 to 150	°C



Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		357	∘c/W

Electrical Characteristics(TJ=25 °C , unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain- Source Breakdown Voltage	V_{GS} =0V , I_{D} =250 uA	60			V
lpss	Drain- Source Leakage Current	V _{DS} =60V , V _{GS} =0V , TJ=25℃			1	ųА
IDSS		V _{DS} =48V , V _{GS} =0V , T _J =125℃			10	ųА
lgss	Gate- Source Leakage Current	$V_{GS*} \pm 20V$, $V_{DS}=0V$			±10	üА

On Characteristics

	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.3A		2.2	2.8	Ω
Rds(on)		V_{GS} =4.5V , I _D =0.2A		24	3 0	Ω
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=250 uA$	1	1.6	2.5	V
gfs	Forward Transconductance	V _{DS} =10V , I _D =0.3A		0.5		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2,3}		 3.7	5.6	
Qgs	Gate-Source Charge ^{2,3}	$V_{\text{DS}}\text{=}30V$, $V_{\text{GS}}\text{=}10V$, $I_{\text{D}}\text{=}1A$	 0.9	1.4	nC
Qgd	Gate-Drain Charge ^{2,3}		 0.4	0.6	
T _{d(on)}	Turn-On Delay Time ^{2,3}		 3	6	
Tr	Rise Time ^{2 , 3}	$V_{\text{DD}}\text{=}30V$, $V_{\text{GS}}\text{=}10V$, $R_{\text{G}}\text{=}6~\Omega$	 5	10	ns
T _{d(off)}	Turn-Off Delay Time ^{2 , 3}	I _D =0.2A	 14	27	115
Tf	Fall Time ^{2,3}		 9	17	
Ciss	Input Capacitance		 25.5	38	
Coss	Output Capacitance	$V_{\text{DS}}\text{=}30\text{V}$, $V_{\text{GS}}\text{=}0\text{V}$, F=1MHz	 17	26	pF
Crss	Reverse Transfer Capacitance		 7.8	12	-

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	V _G =V _D =0V,Force Current			0.3	А
lsм	Pulsed Source Current				1.2	А
Vsd	Diode Forward Voltage	V _{GS} =0V , I _S =1A , TJ=25℃			1.2	V
trr	Reverse Recovery Time	V _{GS} =50V, I _S =1A , dl/dt=100A/µs		3.4		ns
Qrr	Reverse Recovery Charge	TJ=22∘C		0.7		nC

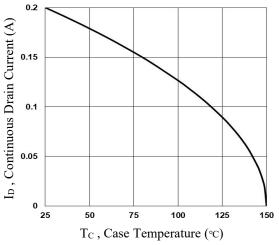
Note :

1.Repetitive Rating : Pulsed width limited by maximum junction temperature.

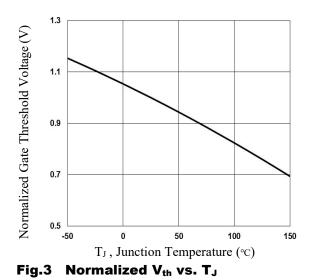
3. Essentially independent of operating temperature.

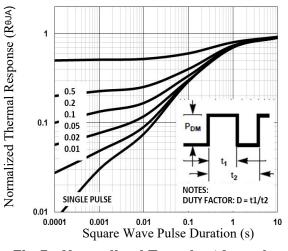
^{2 .} The data tested by pulsed , pulse width \leq 300 us , duty cycle \leq 2%.



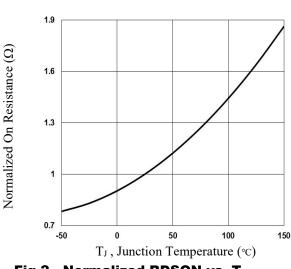














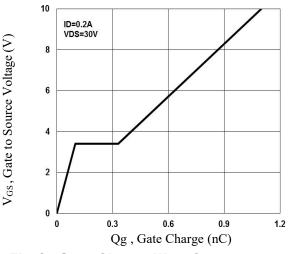


Fig.4 Gate Charge Waveform

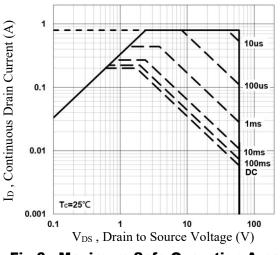
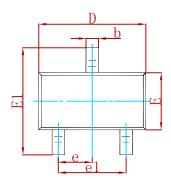
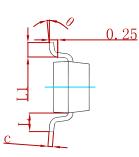
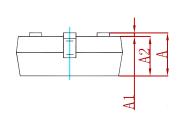


Fig.6 Maximum Safe Operation Area

PACKAGE MECHANICAL DATA

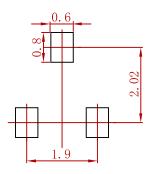






Sumbol	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950) TYP	0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550	REF	0.022	2 REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm. 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2N7002ET1G-MS	SOT-23	3000



2N7002ET1G-MS

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